

Product Summary

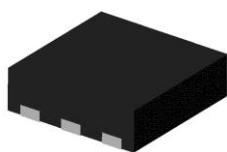
| $V_{(BR)DSS}$ | $R_{DS(ON)}$ Max | I_D Max $T_A = +25^\circ C$ |
|---------------|------------------------|----------------------------------|
| 30V | 15mΩ @ $V_{GS} = 10V$ | 9.3A |
| | 20mΩ @ $V_{GS} = 4.5V$ | 8.1A |

Description

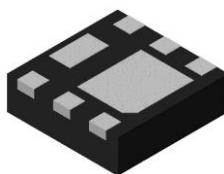
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

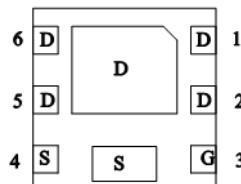
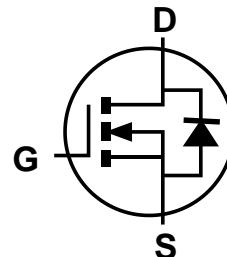
U-DFN2020-6 (Type F)



Top View



Bottom View


 Pin Out
Bottom View


Internal Schematic

Ordering Information (Note 4)

| Part Number | Case | Packaging |
|----------------|----------------------|--------------------|
| DMN3021LFDF-7 | U-DFN2020-6 (Type F) | 3,000/Tape & Reel |
| DMN3021LFDF-13 | U-DFN2020-6 (Type F) | 10,000/Tape & Reel |

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



F2 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: D = 2016)
 M = Month (ex: 9 = September)

Date Code Key

| Year | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 | | | | |
|-------|------|------|------|------|------|------|------|------|-----|-----|-----|-----|
| Code | D | E | F | G | H | I | J | K | | | | |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|---|-----------------|--|-----------|-------------|-------------|
| Drain-Source Voltage | | | V_{DSS} | 30 | V |
| Gate-Source Voltage | | | V_{GSS} | ± 20 | V |
| Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$ | Steady State | $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$ | I_D | 9.3 7.5 | A |
| | $t < 5\text{s}$ | $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$ | I_D | 11.8 9.4 | A |
| Pulsed Drain Current (380 μs Pulse, Duty Cycle = 1%) | | | I_{DM} | 50 | A |
| Maximum Continuous Drain-Source Diode Forward Current (Note 6) | | | I_S | 1.8 | A |
| Avalanche Current (Note 7) $L = 0.1\text{mH}$ | | | I_{AS} | 18 | A |
| Repetitive Avalanche Energy (Note 7) $L = 0.1\text{mH}$ | | | E_{AS} | 16 | mJ |

Thermal Characteristics

| Characteristic | | Symbol | Value | Unit |
|--|---------------------------|-----------------|-------------|--------------------|
| Total Power Dissipation (Note 5) | $T_A = +25^\circ\text{C}$ | P_D | 0.73 | W |
| | $T_A = +70^\circ\text{C}$ | | 0.47 | |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | $R_{\Theta JA}$ | 174 | $^\circ\text{C/W}$ |
| | $t < 5\text{s}$ | | 112 | |
| Total Power Dissipation (Note 6) | $T_A = +25^\circ\text{C}$ | P_D | 2.03 | W |
| | $T_A = +70^\circ\text{C}$ | | 1.30 | |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | $R_{\Theta JA}$ | 64 | $^\circ\text{C/W}$ |
| | $t < 5\text{s}$ | | 40 | |
| Thermal Resistance, Junction to Case (Note 6) | Steady State | $R_{\Theta JC}$ | 13 | |
| Operating and Storage Temperature Range | T_J, T_{STG} | | -55 to +150 | $^\circ\text{C}$ |

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---------------------|-----|-----|-----------|------------------|---|
| OFF CHARACTERISTICS (Note 8) | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | 30 | — | — | V | $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$ |
| Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$ | I_{DSS} | — | — | 1 | μA | $V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$ |
| Gate-Source Leakage | I_{GSS} | — | — | ± 100 | nA | $V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$ |
| ON CHARACTERISTICS (Note 8) | | | | | | |
| Gate Threshold Voltage | $V_{GS(\text{TH})}$ | 1.0 | — | 2.2 | V | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$ |
| Static Drain-Source On-Resistance | $R_{DS(\text{ON})}$ | — | — | 15 | $\text{m}\Omega$ | $V_{GS} = 10\text{V}, I_D = 7\text{A}$ |
| | | | — | 20 | | $V_{GS} = 4.5\text{V}, I_D = 7\text{A}$ |
| Diode Forward Voltage | V_{SD} | — | 0.8 | 1.2 | V | $V_{GS} = 0\text{V}, I_S = 2.2\text{A}$ |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | |
| Input Capacitance | C_{ISS} | — | 706 | — | pF | $V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$ |
| Output Capacitance | C_{OSS} | — | 112 | — | | |
| Reverse Transfer Capacitance | C_{RSS} | — | 81 | — | | |
| Gate Resistance | R_G | — | 2.6 | — | Ω | $V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ |
| Total Gate Charge ($V_{GS} = 10\text{V}$) | Q_G | — | 14 | — | nC | $V_{DS} = 15\text{V}, I_D = 5\text{A}$ |
| Total Gate Charge ($V_{GS} = 4.5\text{V}$) | Q_G | — | 6.7 | — | | |
| Gate-Source Charge | Q_{GS} | — | 1.9 | — | | |
| Gate-Drain Charge | Q_{GD} | — | 2.5 | — | | |
| Turn-On Delay Time | $t_{D(\text{ON})}$ | — | 5.4 | — | ns | $V_{DS} = 15\text{V}, V_{GS} = 4.5\text{V}, R_G = 1.7\Omega, I_D = 5\text{A}$ |
| Turn-On Rise Time | t_R | — | 6.8 | — | | |
| Turn-Off Delay Time | $t_{D(\text{OFF})}$ | — | 9.7 | — | | |
| Turn-Off Fall Time | t_F | — | 4.7 | — | | |

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

7. I_{AS} and EAS rating are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

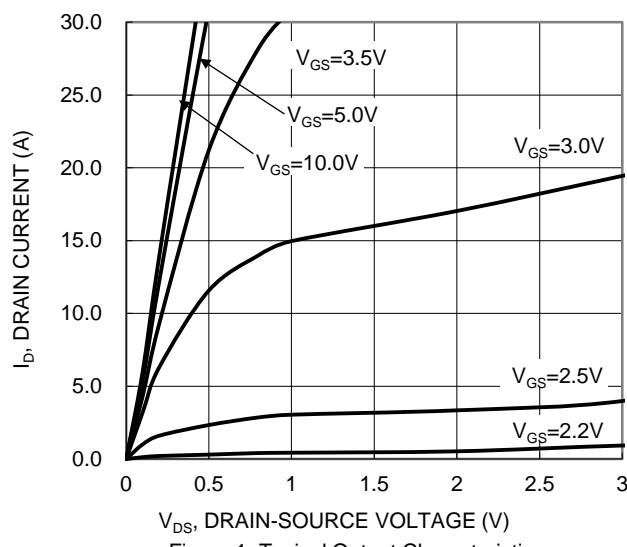


Figure 1. Typical Output Characteristic

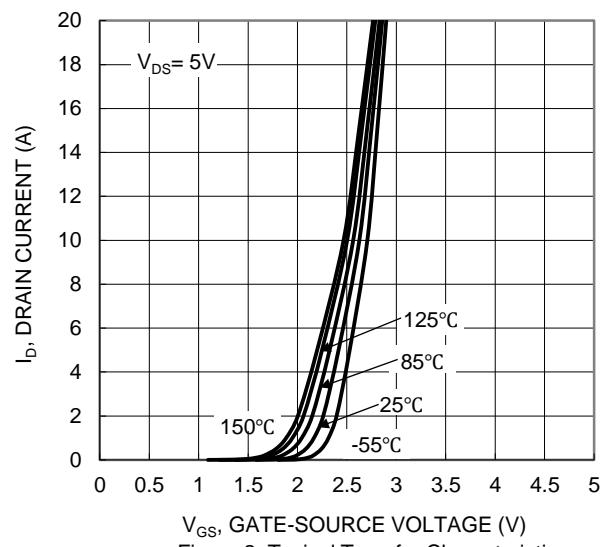


Figure 2. Typical Transfer Characteristic

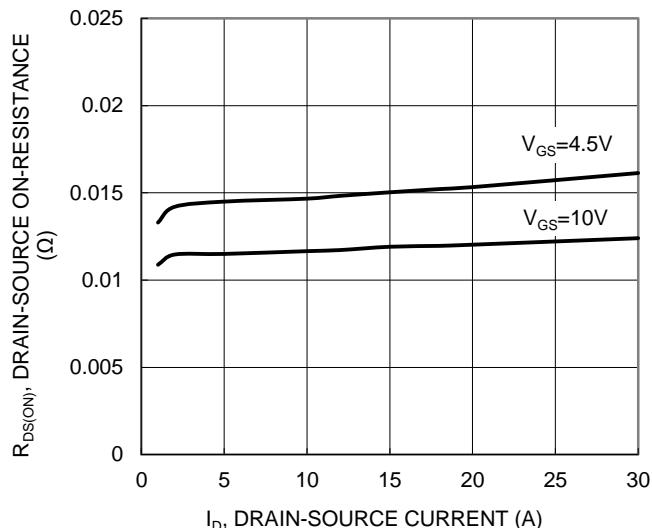


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

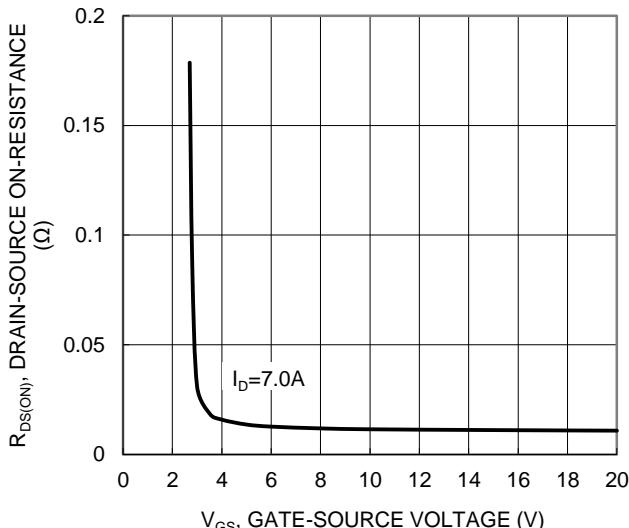


Figure 4. Typical Transfer Characteristic

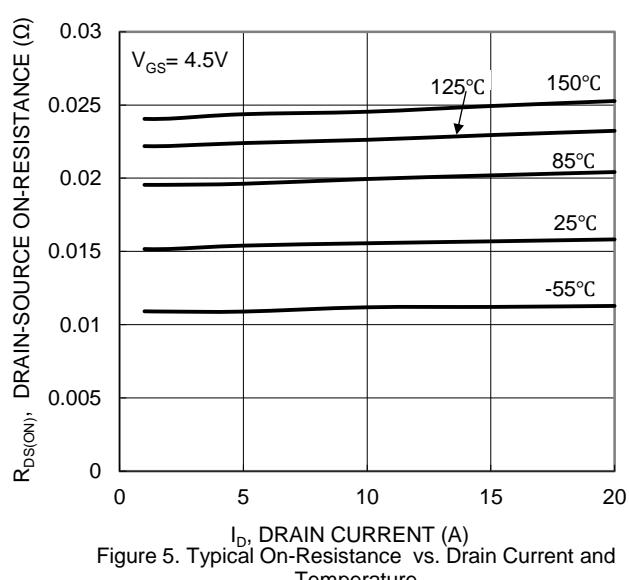


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

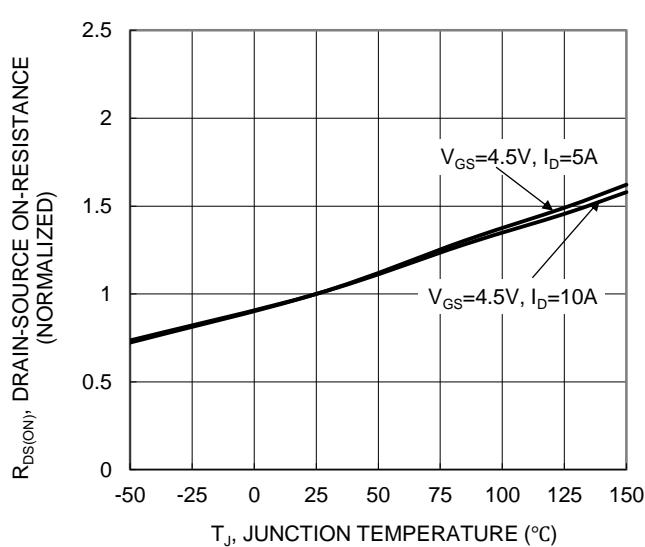
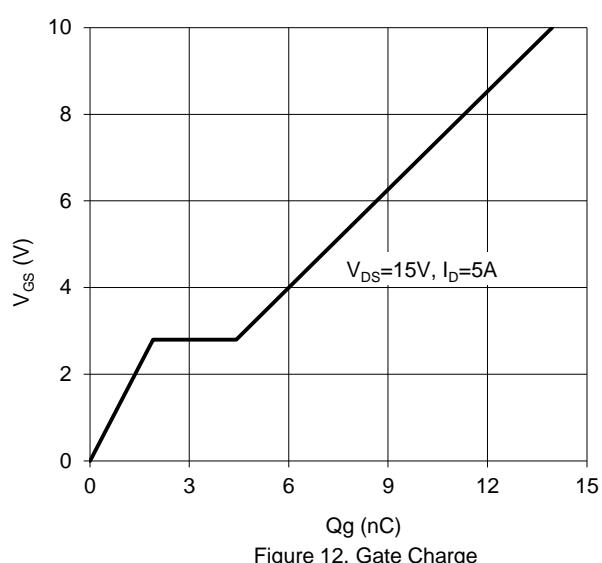
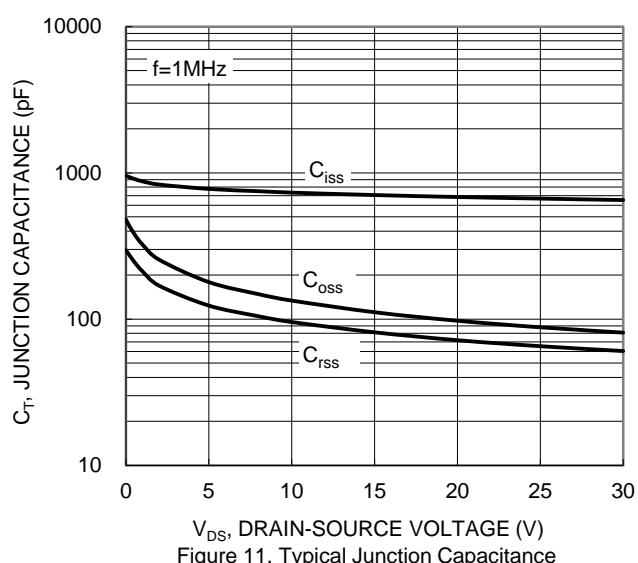
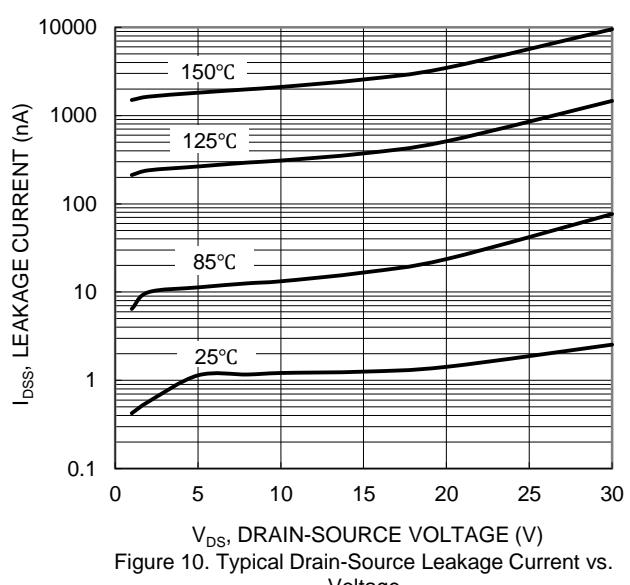
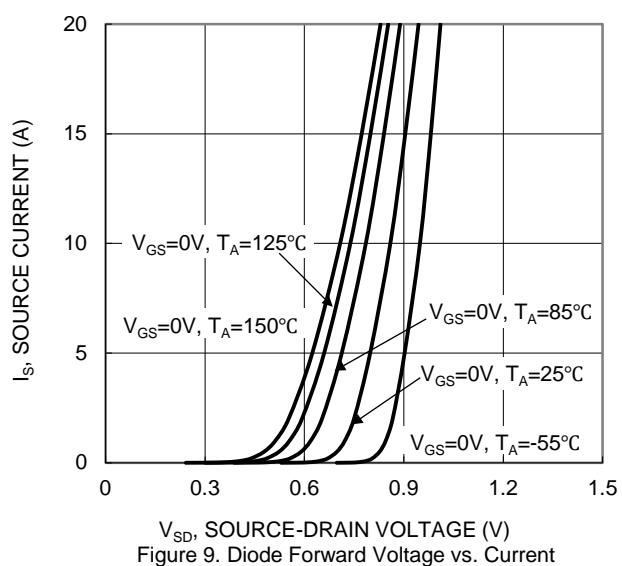
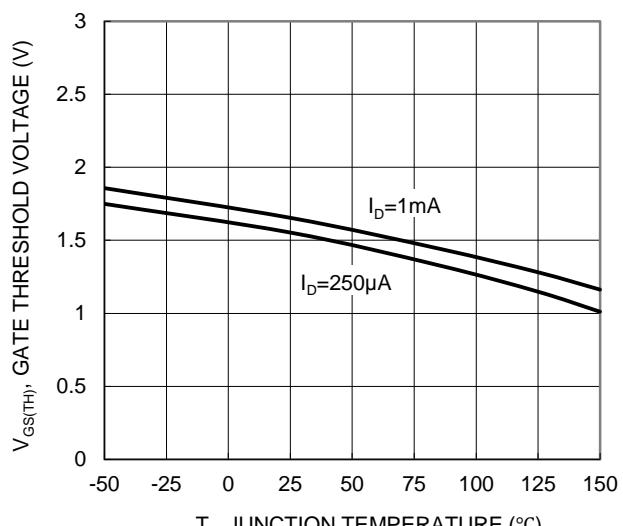
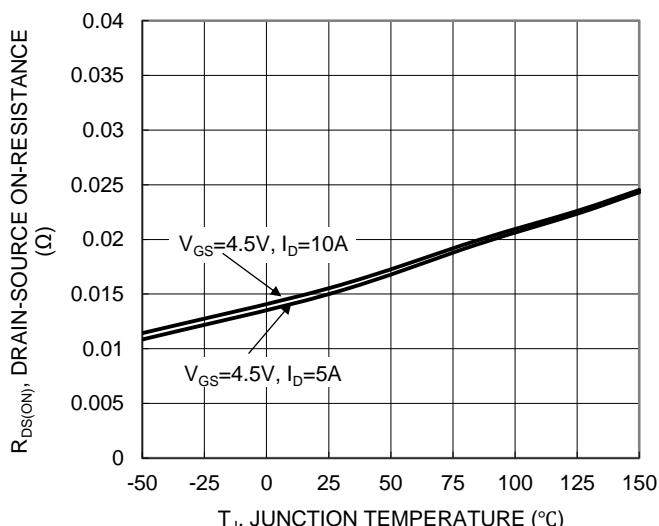
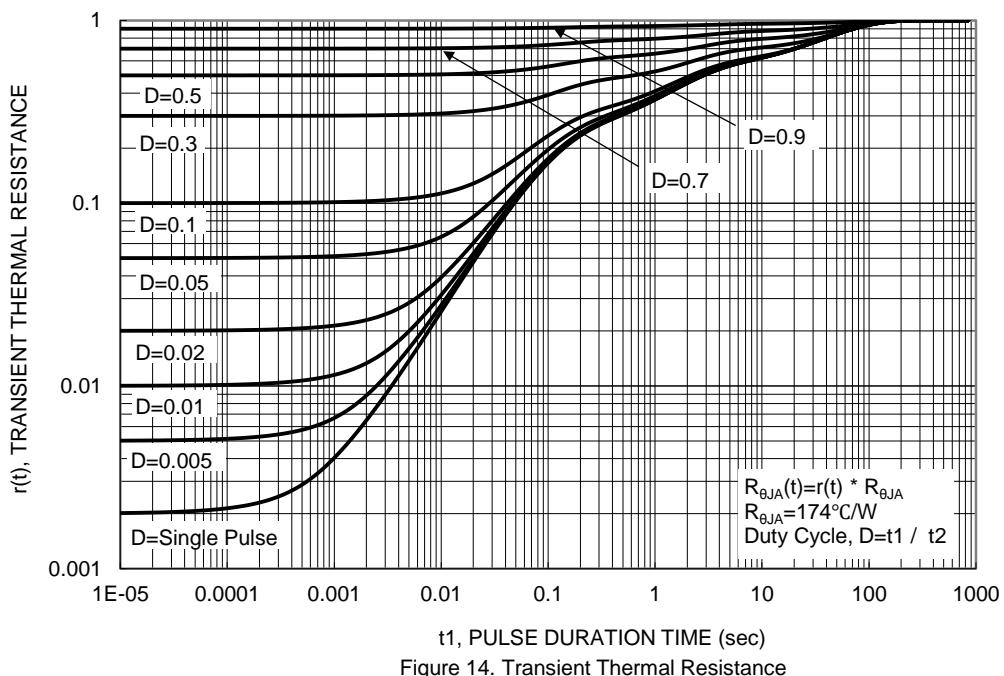
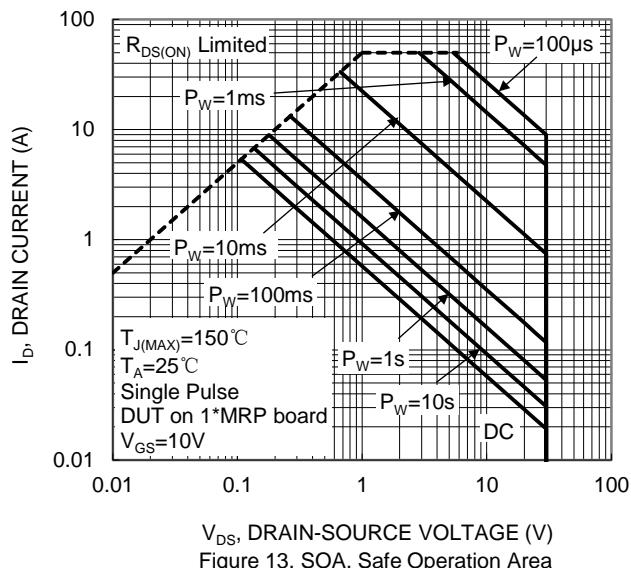


Figure 6. On-Resistance Variation with Temperature

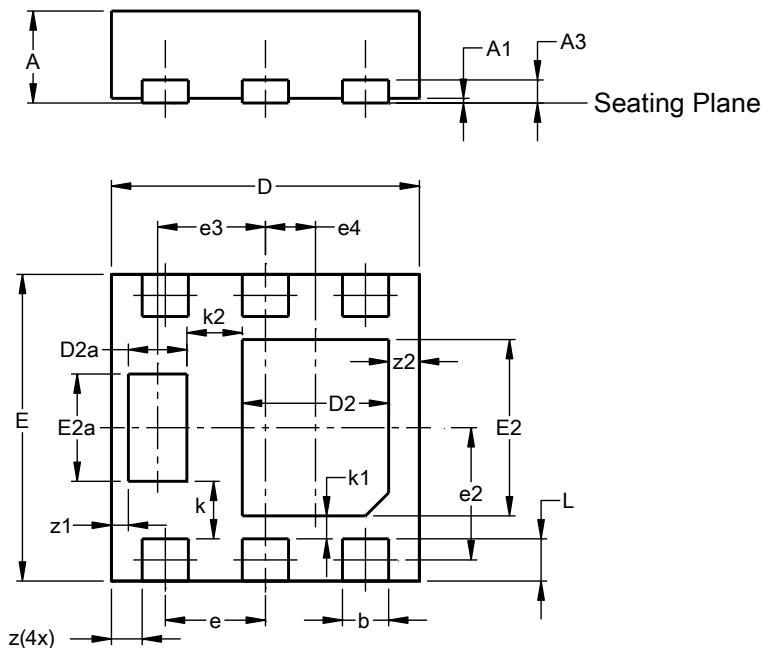




Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)

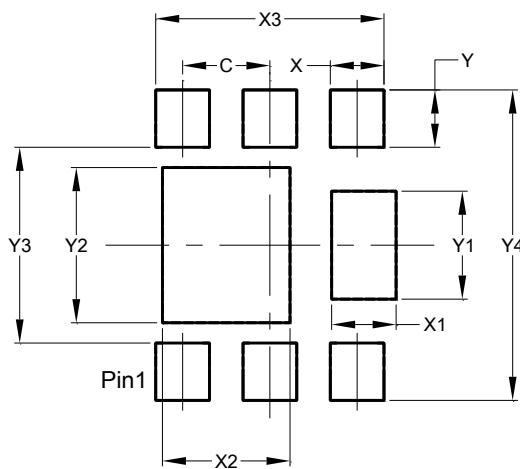


| U-DFN2020-6 (Type F) | | | |
|-------------------------|-----------|-------|-------|
| Dim | Min | Max | Typ |
| A | 0.57 | 0.63 | 0.60 |
| A1 | 0.00 | 0.05 | 0.03 |
| A3 | - | - | 0.15 |
| b | 0.25 | 0.35 | 0.30 |
| D | 1.95 | 2.05 | 2.00 |
| D2 | 0.85 | 1.05 | 0.95 |
| D2a | 0.33 | 0.43 | 0.38 |
| E | 1.95 | 2.05 | 2.00 |
| E2 | 1.05 | 1.25 | 1.15 |
| E2a | 0.65 | 0.75 | 0.70 |
| e | 0.65 BSC | | |
| e2 | 0.863 BSC | | |
| e3 | 0.70 BSC | | |
| e4 | 0.325 BSC | | |
| k | 0.37 BSC | | |
| k1 | 0.15 BSC | | |
| k2 | 0.36 BSC | | |
| L | 0.225 | 0.325 | 0.275 |
| z | 0.20 BSC | | |
| z1 | 0.110 BSC | | |
| z2 | 0.20 BSC | | |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 0.650 |
| X | 0.400 |
| X1 | 0.480 |
| X2 | 0.950 |
| X3 | 1.700 |
| Y | 0.425 |
| Y1 | 0.800 |
| Y2 | 1.150 |
| Y3 | 1.450 |
| Y4 | 2.300 |

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